



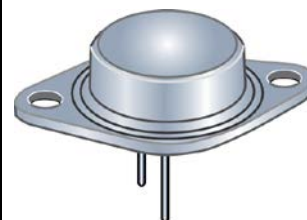
PNP Darlington Power Silicon Transistor

Qualified per MIL-PRF-19500/501

Qualified Levels:
JAN, JANTX, and
JANTXV

DESCRIPTION

This high speed PNP transistor is rated at 12 amps and is military qualified up to a JANTXV level. This TO-204AA isolated package features a 180 degree lead orientation.



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FEATURES

- JEDEC registered 2N6051 and 2N6052
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/501
- RoHS compliant versions available (commercial grade only)

**TO-204AA (TO-3)
Package**

APPLICATIONS / BENEFITS

- Military, space and other high reliability applications
- High frequency response
- TO-204AA case with isolated terminals

MAXIMUM RATINGS @ $T_C = +25^\circ\text{C}$ unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-55 to +175	$^\circ\text{C}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Collector Current	I_C	-12	A
Collector-Emitter Voltage	V_{CEO}	2N6051 -80	V
		2N6052 -100	
Collector-Base Voltage	V_{CBO}	2N6051 -80	V
		2N6052 -100	
Emitter-Base Voltage	V_{EBO}	-5	V
Total Power Dissipation	P_T	@ $T_C = +25^\circ\text{C}$ ⁽¹⁾ 150	W
		@ $T_C = +100^\circ\text{C}$ 75	

Notes: 1. Derate linearly 1.0 W/ $^\circ\text{C}$ above $T_C > +25^\circ\text{C}$.

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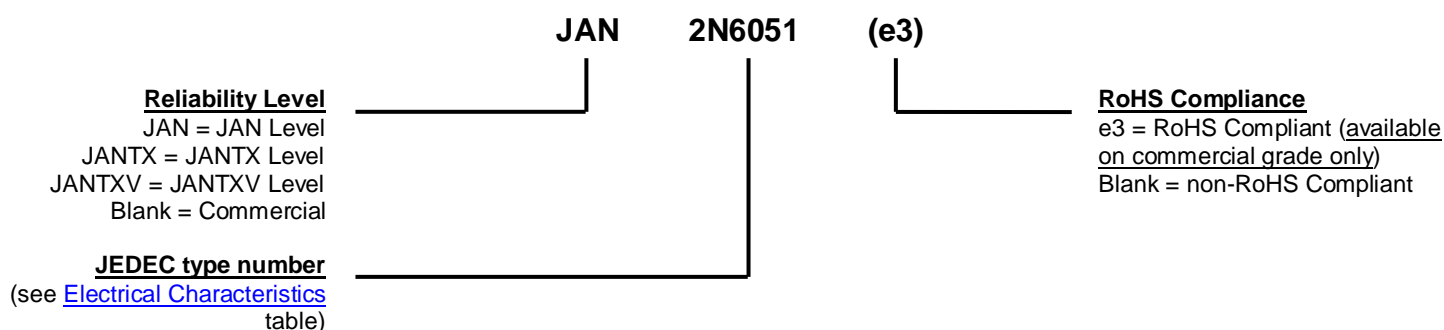
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MECHANICAL and PACKAGING

- CASE: Industry standard TO-204AA (TO-3), hermetically sealed, 0.040 inch diameter pins
- FINISH: Solder dipped tin-lead over nickel plated alloy 52 or RoHS compliant matte-tin plating. Solderable per MIL-STD-750 method 2026.
- POLARITY: PNP (see [schematic](#))
- MOUNTING HARDWARE: Consult factory for optional insulator and sheet metal screws
- WEIGHT: Approximately 15 grams
- See [package dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
I_B	Base current: The value of the dc current into the base terminal.
I_C	Collector current: The value of the dc current into the collector terminal.
I_E	Emitter current: The value of the dc current into the emitter terminal.
T_C	Case temperature: The temperature measured at a specified location on the case of a device.
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.
V_{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
V_{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.
V_{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.
V_{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
V_{EB}	Emitter-base voltage: The dc voltage between the emitter and the base
V_{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$ unless otherwise noted

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = -100\text{ mA}$	2N6051 2N6052	$V_{(BR)CEO}$	-80 -100	V
Collector-Emitter Cutoff Current $V_{CE} = -40\text{ V}$ $V_{CE} = -50\text{ V}$	2N6051 2N6052	I_{CEO}	-1.0 -1.0	mA
Collector-Emitter Cutoff Current $V_{CE} = -80\text{ V}, V_{BE} = 1.5\text{ V}$ $V_{CE} = -100\text{ V}, V_{BE} = 1.5\text{ V}$	2N6051 2N6052	I_{CEX}	-0.01 -0.01	mA
Emitter-Base Cutoff Current $V_{BE} = -5.0\text{ V}$		I_{EBO}	-2.0	mA

ON CHARACTERISTICS

Forward-Current Transfer Ratio $I_C = -1.0\text{ A}, V_{CE} = 3.0\text{ V}$ $I_C = -6.0\text{ A}, V_{CE} = 3.0\text{ V}$ $I_C = -12\text{ A}, V_{CE} = 3.0\text{ V}$		h_{FE}	1,000 1,000 150	18,000
Collector-Emitter Saturation Voltage $I_C = -12\text{ A}, I_B = -120\text{ mA}$ $I_C = -6.0\text{ A}, I_B = -24\text{ mA}$		$V_{CE(sat)}$	-3.0 -2.0	V
Base-Emitter Saturation Voltage $I_C = -12\text{ A}, I_B = -120\text{ mA}$		$V_{BE(sat)}$	-4.0	V
Base-Emitter Voltage Non-saturated $V_{CE} = -3.0\text{ V}, I_C = -6\text{ A}$		V_{BE}	-2.8	V

DYNAMIC CHARACTERISTICS

Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -5\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ kHz}$		h_{fe}	1,000	
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = -5\text{ A}, V_{CE} = -3.0\text{ V}, f = 1\text{ MHz}$		$ h_{fe} $	10	250
Output Capacitance $V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz} \leq f \leq 1\text{ MHz}$		C_{obo}	300	pF

ELECTRICAL CHARACTERISTICS @ $T_C = 25^\circ\text{C}$ unless otherwise noted. (continued)**SWITCHING CHARACTERISTICS**

Turn-On Time $V_{CC} = -30\text{ V}$, $I_C = -5\text{ A}$; $I_{B1} = -20\text{ mA}$	t_{on}		2.0	μs
Turn-Off Time $V_{CC} = -30\text{ V}$, $I_C = -5\text{ A}$; $I_{B1} = I_{B2} = -20\text{ mA}$	t_{off}		10	μs

SAFE OPERATING AREA (See [Figures 1 and 2](#) and [MIL-STD-750, Test Method 3053](#))**DC Tests** $T_C = +25^\circ\text{C}$, $+10^\circ\text{C}$, -0°C , $t \geq 1\text{ second}$, 1 Cycle**Test 1** $V_{CE} = -12.5\text{ V}$, $I_C = -12\text{ A}$ **Test 2** $V_{CE} = -30\text{ V}$, $I_C = -5\text{ A}$ **Test 3** $V_{CE} = -70\text{ V}$, $I_C = -200\text{ mA}$ (2N6051) $V_{CE} = -90\text{ V}$, $I_C = -155\text{ mA}$ (2N6052)

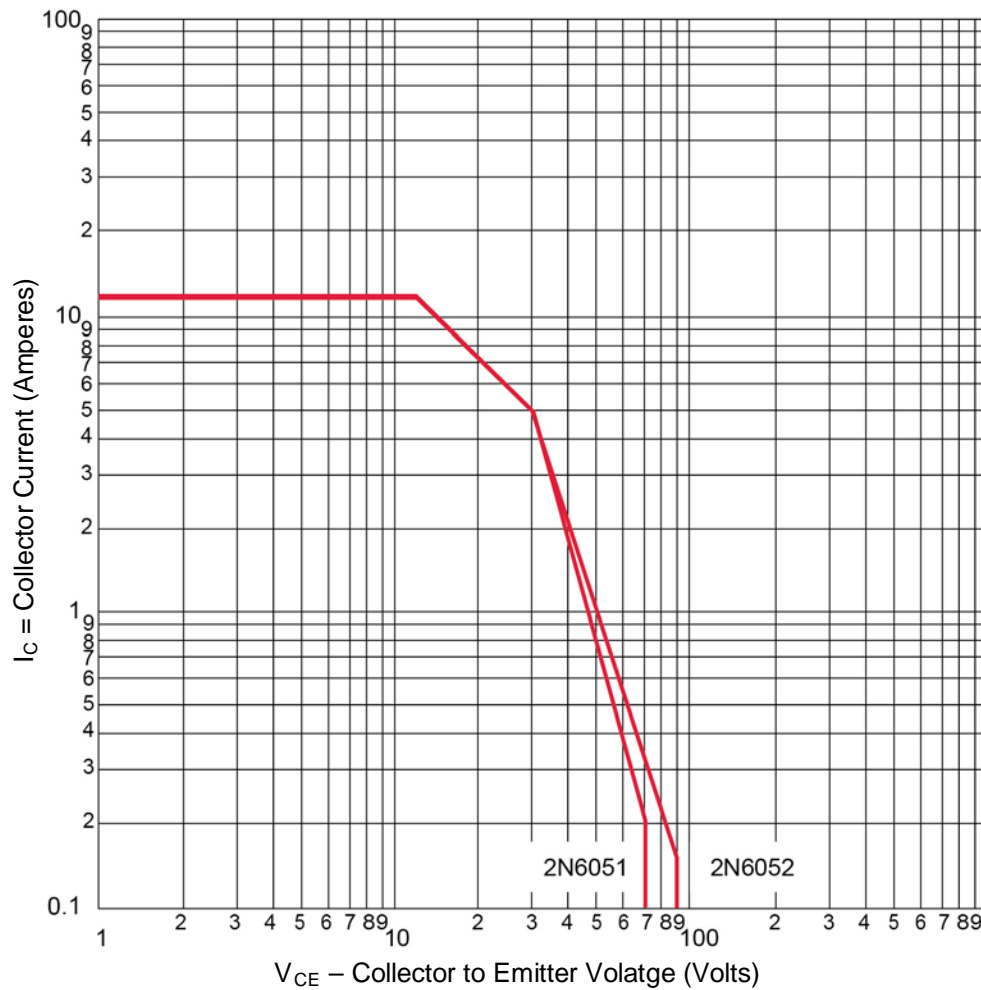
SAFE OPERATING AREA


FIGURE 1
Maximum Safe Operating Area
 (continuous dc)

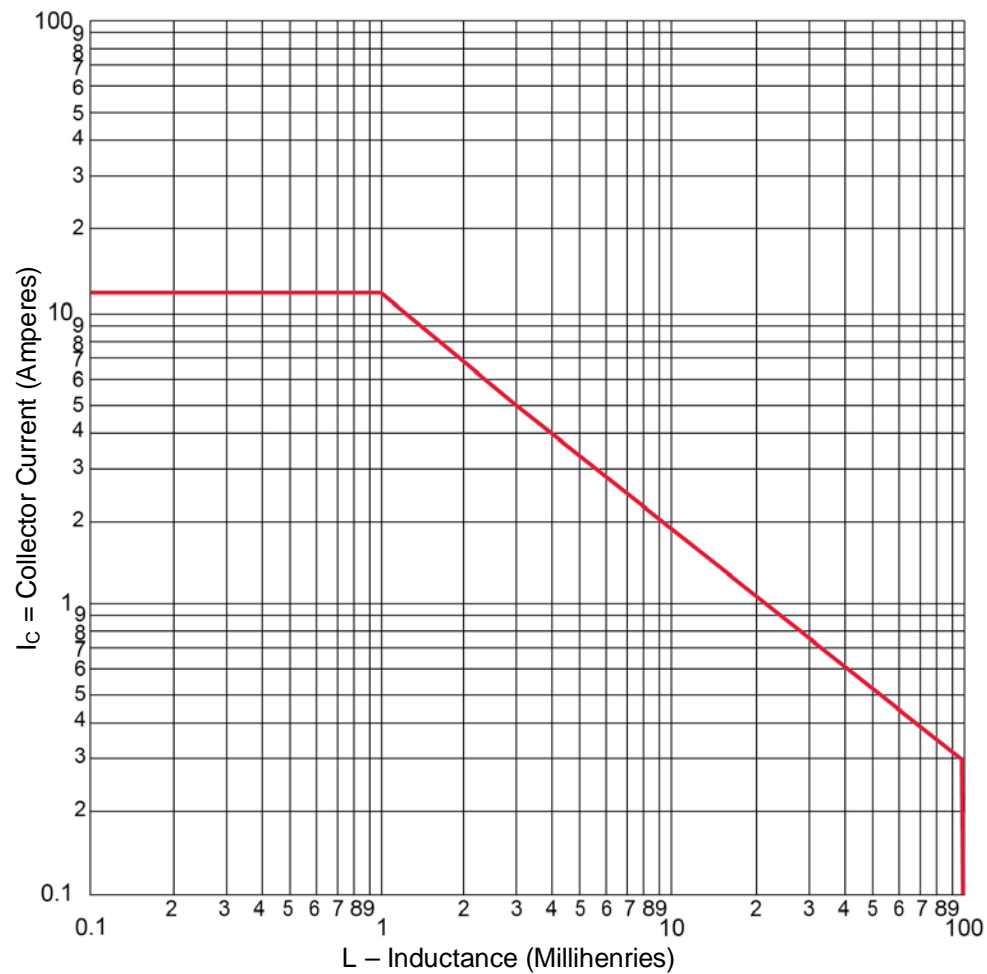
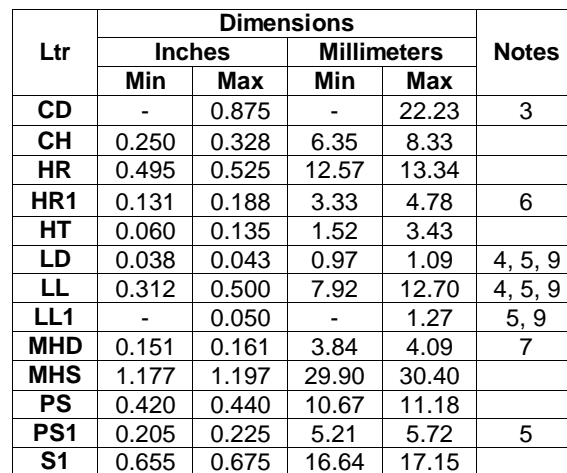
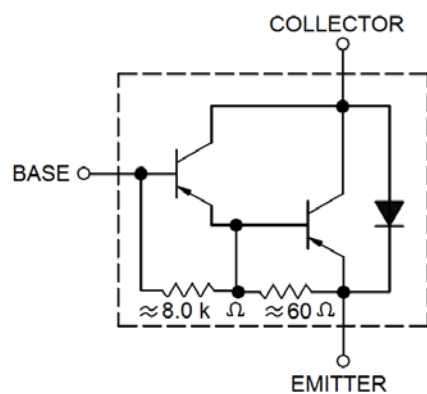
SAFE OPERATING AREA (continued)


FIGURE 2
Safe Operating Area for Switching Between Saturation and Cutoff
(unclamped inductive load).

PACKAGE DIMENSIONS



1. Dimensions are in inches. Millimeters are given for information only.
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3. Body contour is optional within zone defined by CD.
4. These dimensions shall be measured at points .050 inch (1.27 mm) to .055 inch (1.40 mm) below seating plane. When gauge is not used, measurement shall be made at seating plane.
5. Both terminals.
6. At both ends.
7. Two holes.
8. The collector shall be electrically connected to the case.
9. LD applies between L1 and LL. Lead diameter shall not exceed twice LD within L1.
10. The seating plane of the header shall be flat within .001 inch (0.03 mm), concave to .004 inch (0.10 mm), convex inside a .930 inch (23.62 mm) diameter circle on the center of the header, and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm), convex overall.
11. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

SCHEMATIC

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